

HiPerFET™

Power MOSFETs

Q-Class

Single MOSFET Die

N-Channel Enhancement Mode
Avalanche Rated, Low Q_g , High dv/dt

IXFN 21N100Q

$V_{DSS} = 1000 \text{ V}$

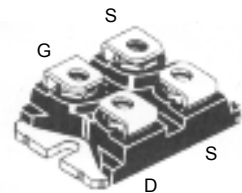
$I_{D25} = 21 \text{ A}$

$R_{DS(on)} = 0.50 \Omega$

$t_{rr} \leq 250 \text{ ns}$



miniBLOC, SOT-227 B (IXFN)
E153432



G = Gate
S = Source

D = Drain

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	1000	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	21	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	84	A
I_{AR}	$T_C = 25^\circ\text{C}$	21	A
E_{AR}	$T_C = 25^\circ\text{C}$	60	mJ
E_{AS}		2.5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	520	W
T_J		-55 to +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 to +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$ $I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	2500 3000	V~ V~
M_d	Mounting torque Terminal connection torque	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
Weight		30	g

Features

- IXYS advanced low Q_g process
- Low gate charge and capacitances
 - easier to drive
 - faster switching
- Unclamped Inductive Switching (UIS) rated
- Low $R_{DS(on)}$
- Fast intrinsic diode
- International standard package
- miniBLOC with Aluminium nitride isolation for low thermal resistance
- Low terminal inductance (<10 nH) and stray capacitance to heatsink (<35 pF)
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

Advantages

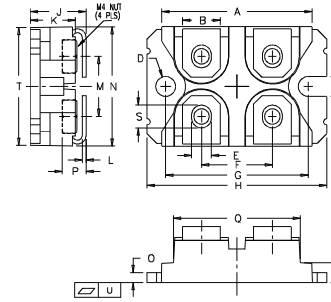
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 1 \text{ mA}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4 \text{ mA}$	3		5.0 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			100 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			0.50 Ω

Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	V _{DS} = 20 V; I _D = 0.5 • I _{D25} , pulse test	16	22	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		5900	pF
C_{oss}			550	pF
C_{rss}			90	pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25} R _G = 1 Ω (External)		21	ns
t_{rr}			18	ns
t_{d(off)}			60	ns
t_f			12	ns
Q_{G(on)}	V _{GS} = 10 V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25}		170	nC
Q_{GS}			38	nC
Q_{GD}			75	nC
R_{thJC}			0.05	0.24 K/W
R_{thCK}				K/W

Source-Drain Diode		Characteristic Values (T _J = 25°C, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	V _{GS} = 0 V			21 A
I_{SM}	Repetitive; pulse width limited by T _{JM}			84 A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
t_{rr}	I _F = I _S , -di/dt = 100 A/μs, V _R = 100 V		1.4	250 ns
Q_{RM}				μC
I_{RM}				A

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	

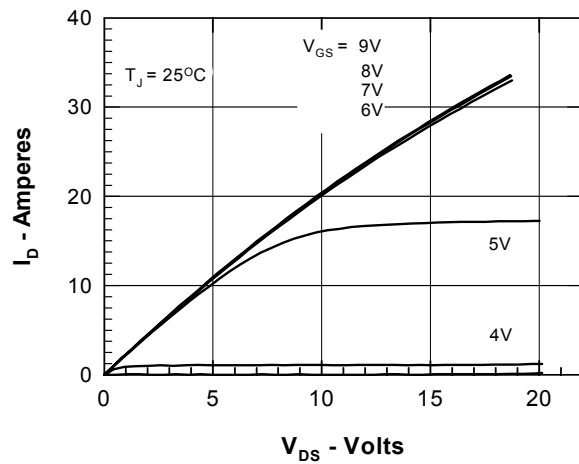


Fig.1 Output Characteristics @ $T_J = 25^\circ\text{C}$

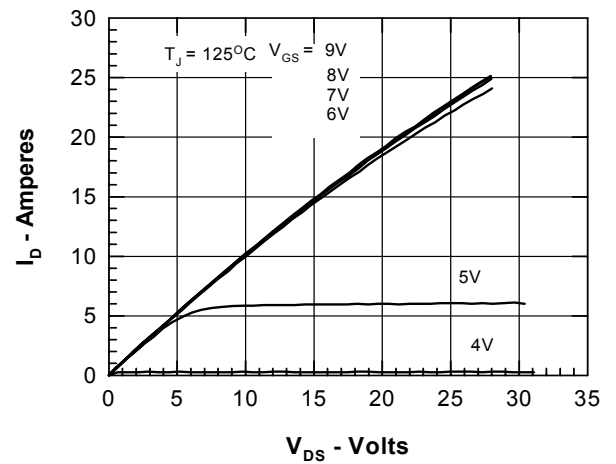


Fig.2 Output Characteristics @ $T_J = 125^\circ\text{C}$

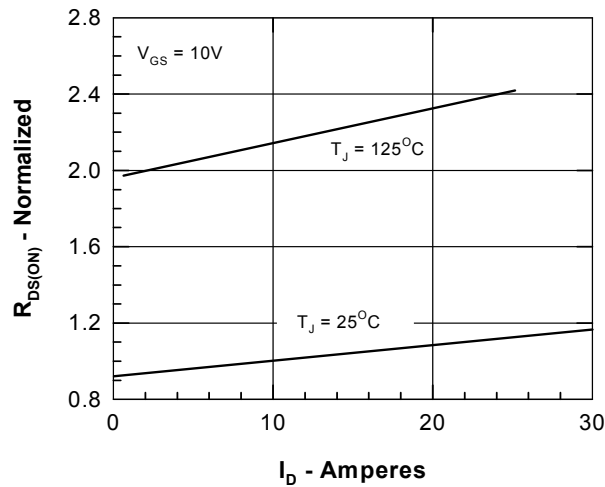


Fig.3 $R_{DS(on)}$ vs. Drain Current

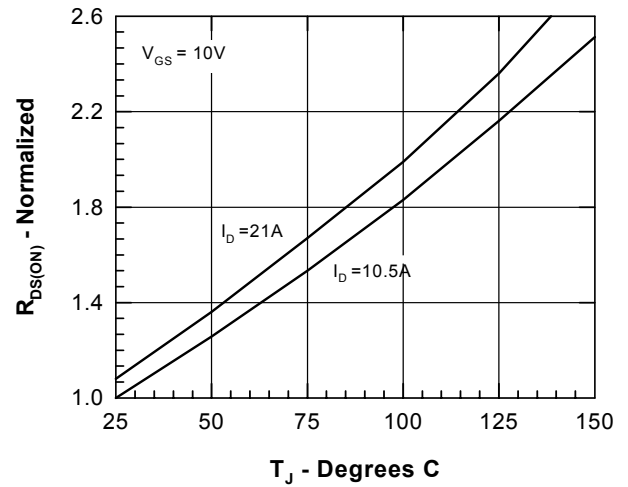


Fig.4 Temperature Dependence of Drain to Source Resistance

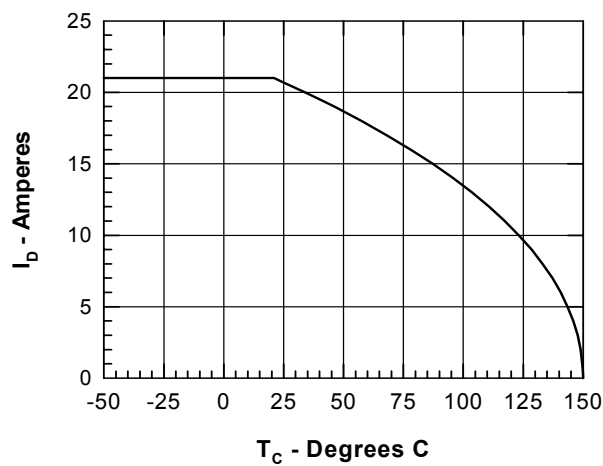


Fig.5 Drain Current vs. Case Temperature

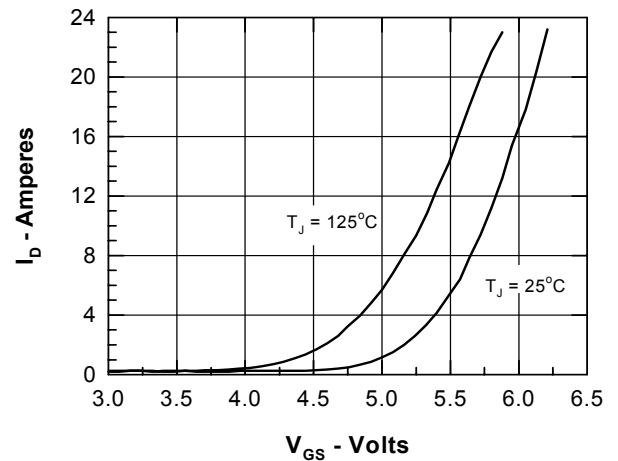


Fig.6 Drain Current vs Gate Source Voltage

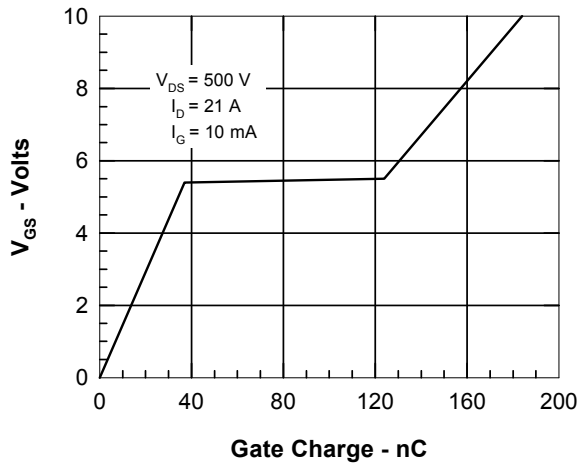


Fig.7 Gate Charge Characteristic Curve

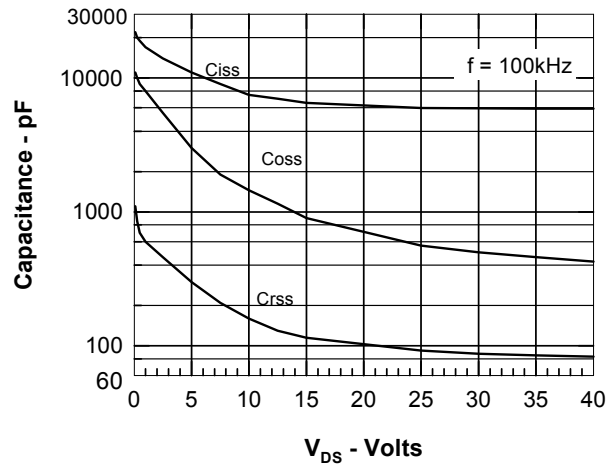


Fig.8 Capacitance Curves

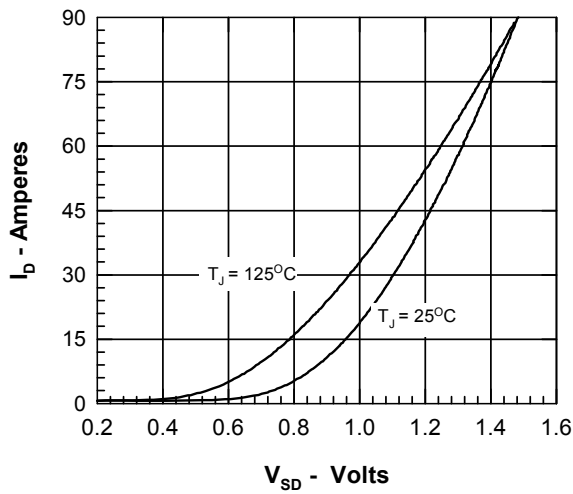


Fig.9 Drain Current vs Drain to Source Voltage

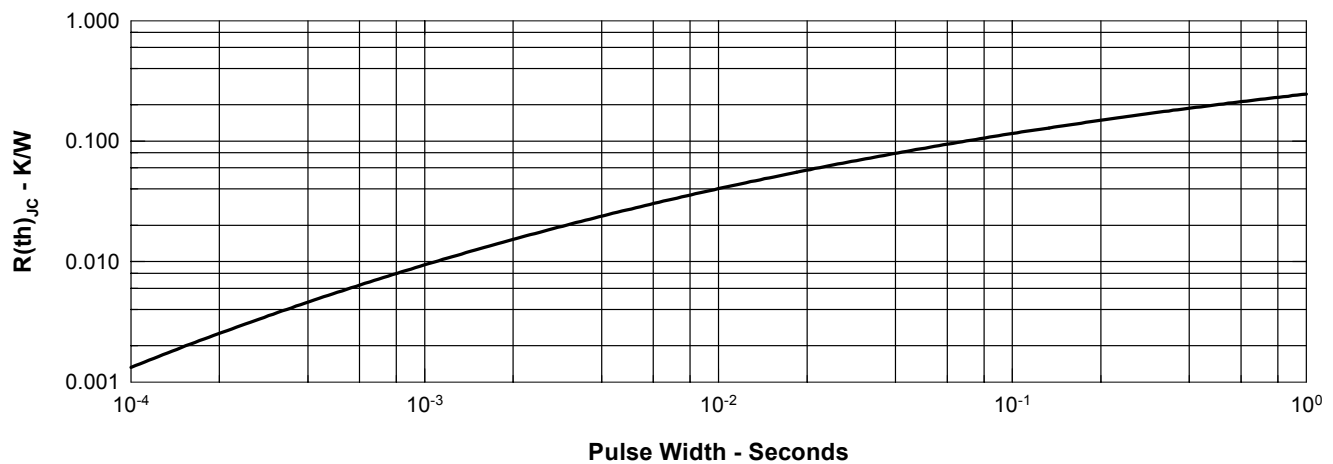


Fig.10 Transient Thermal Impedance

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